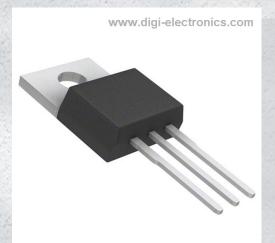


FJP5021 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number FJP5021-DG

Manufacturer onsemi

Manufacturer Product Number FJP5021

Description TRANS NPN 500V 5A TO220-3

Detailed Description Bipolar (BJT) Transistor NPN 500 V 5 A 18MHz 50 W

Through Hole TO-220-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FJP5021	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	5 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
500 V	1V @ 600mA, 3A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
10μA (ICBO)	15 @ 600mA, 5V
Power - Max:	Frequency - Transition:
50 W	18MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-220-3	TO-220-3
Base Product Number:	
FJP5021	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FARQQ	8541 29 0095



FJP5021

High Voltage and High Reliability

- High Speed Switching : $t_F = 0.1 \mu s$ (Typ.)
- Wide SOA



1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	5	Α
I _{CP}	Collector Current (Pulse)	10	Α
I _B	Base Current	2	Α
P _C	P _C Collector Dissipation (T _C =25°C)		W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	800			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	500			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 2.5A$, $I_{B1} = -I_{B2} = 1A$ L = 1mH, Clamped	500			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.6A$	15		50	
h _{FE2}		$V_{CE} = 5V$, $I_C = 3A$	8			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1.5	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f=1MHz$		80		pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.6A$		18		MHz
t _{ON}	Turn On Time	V _{CC} = 200V			0.5	μs
t _{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$			3	μs
t _F	Fall Time	$R_L = 50\Omega$		0.1	0.3	μs

h_{FE} Classification

Classification	R	0	Y
h _{FE1}	15 ~ 30	20 ~ 40	30 ~ 50

Typical Characteristics

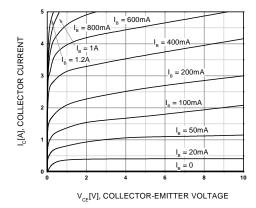


Figure 1. Static Characteristic

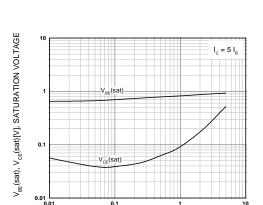


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

 $I_c[A]$, COLLECTOR CURRENT

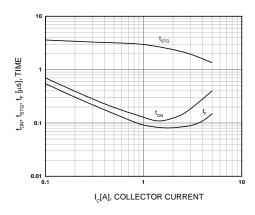


Figure 5. Switching Time

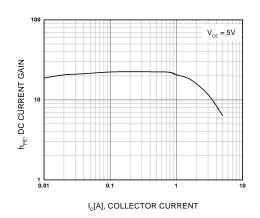


Figure 2. DC current Gain

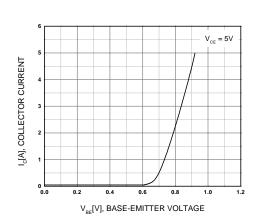


Figure 4. Base-Emitter On Voltage

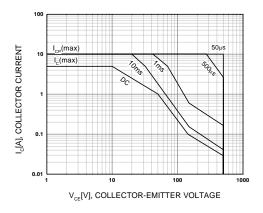


Figure 6. Forward Bias Safe Operating Area

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Typical Characteristics (Continued)

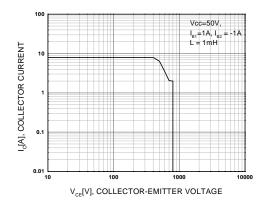


Figure 7. Reverse Bias Safe Operating Area

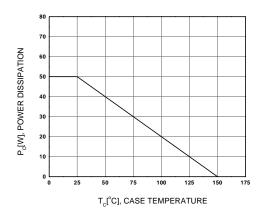
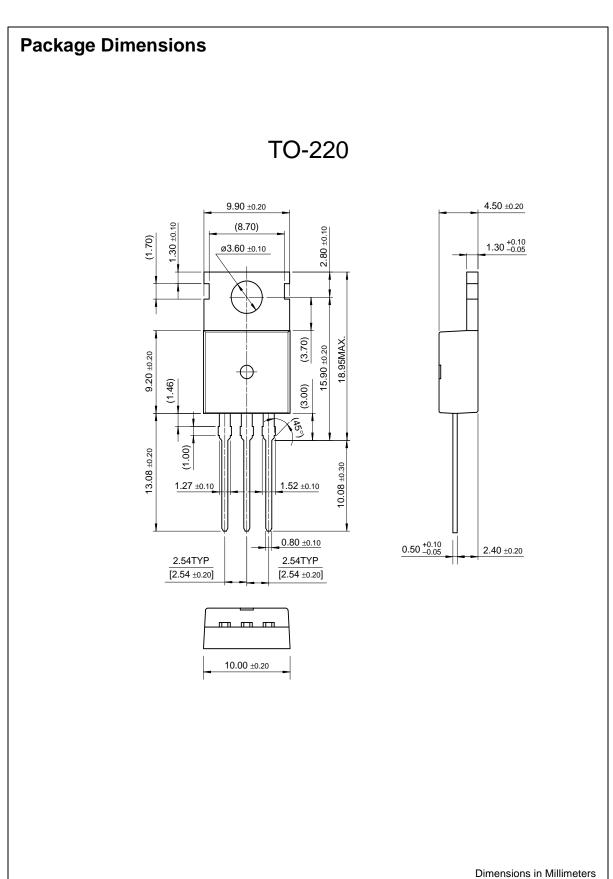


Figure 8. Power Derating



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E ² CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I^2C^{TM}	OCX^{TM}	RapidConfigure™	UHC™
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The Power Franc	hise™	OPTOLOGIC [®]	SILENT SWITCHER®	VCX™
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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